

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

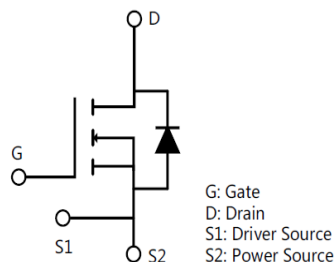
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	850	V
$I_D, pulse$	45	A
$R_{DS(ON), max} @ V_{GS}=10V$	300	m Ω
Q_g	23.3	nC

Marking Information

Product Name	Package	Marking
OSG80R300JF	PDFN 8x8	OSG80R300J

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	15	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		9.5	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	45	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	15	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	45	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	151	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	360	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.83	$^\circ\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	800			V	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$
		850				$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$, $T_j=150^\circ\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.24	0.3	Ω	$V_{GS}=10\text{ V}$, $I_D=7.5\text{ A}$
			0.64			$V_{GS}=10\text{ V}$, $I_D=7.5\text{ A}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			5	μA	$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$
Gate resistance	R_G		18.2		Ω	$f=1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1552		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		80.1		pF	
Reverse transfer capacitance	C_{rss}		2.1		pF	
Turn-on delay time	$t_{d(on)}$		33.6		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=7.5\text{ A}$
Rise time	t_r		20.3		ns	
Turn-off delay time	$t_{d(off)}$		57.9		ns	
Fall time	t_f		4.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		22.7		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=7.5\text{ A}$
Gate-source charge	Q_{gs}		8.6		nC	
Gate-drain charge	Q_{gd}		2.3		nC	
Gate plateau voltage	$V_{plateau}$		5.5		V	

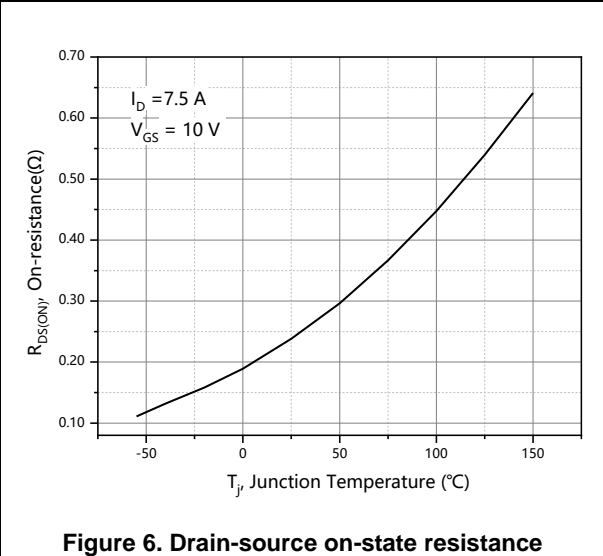
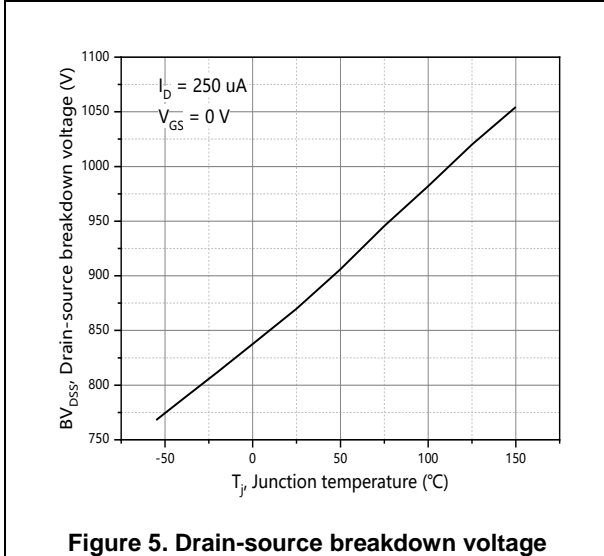
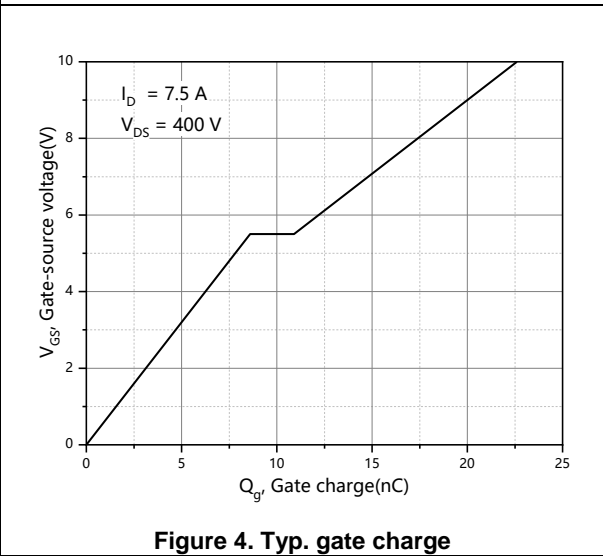
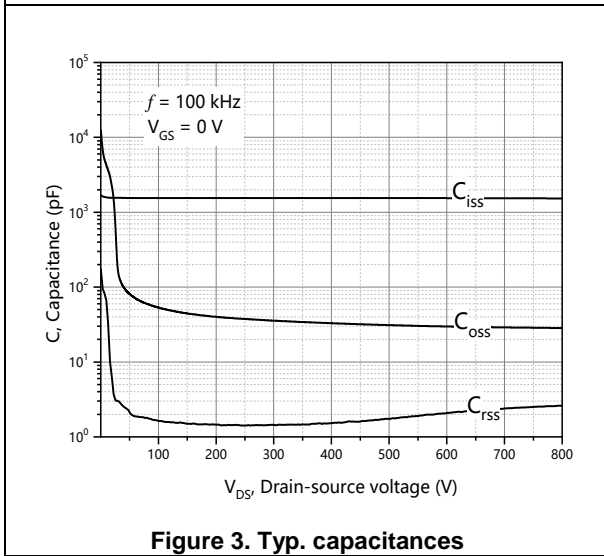
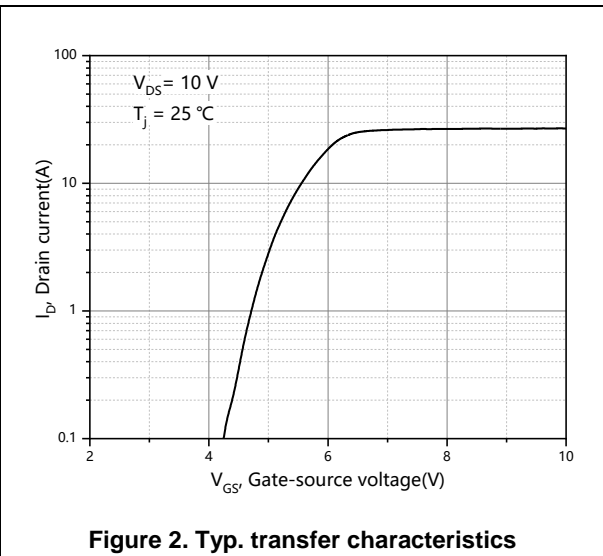
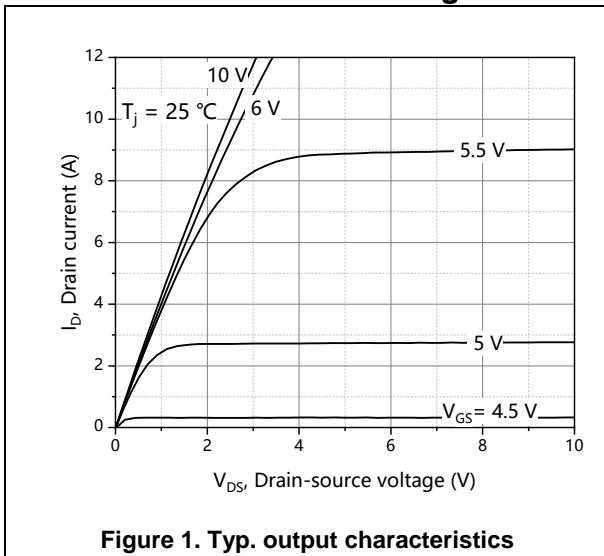
Body Diode Characteristics

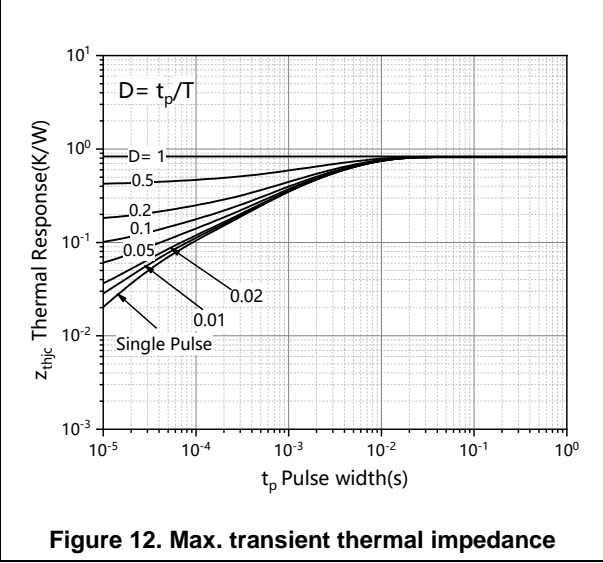
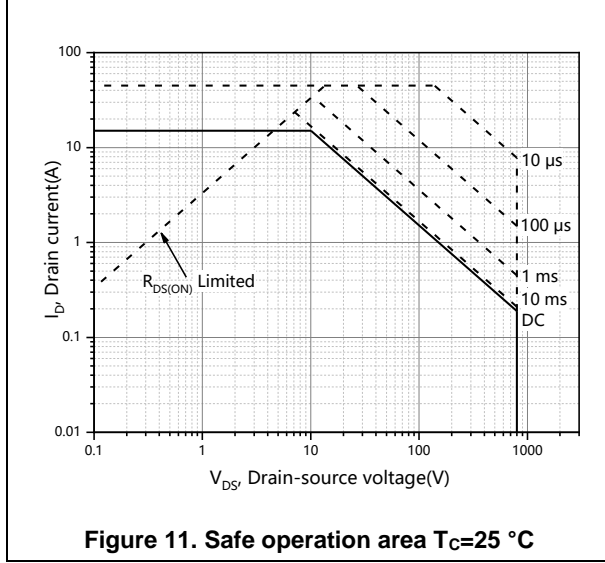
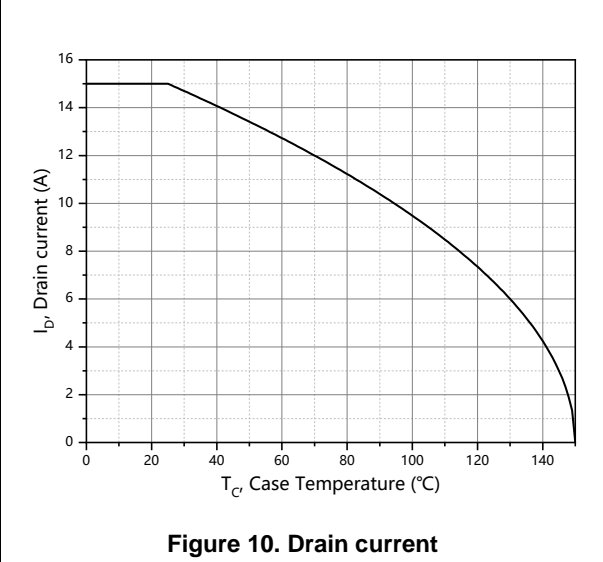
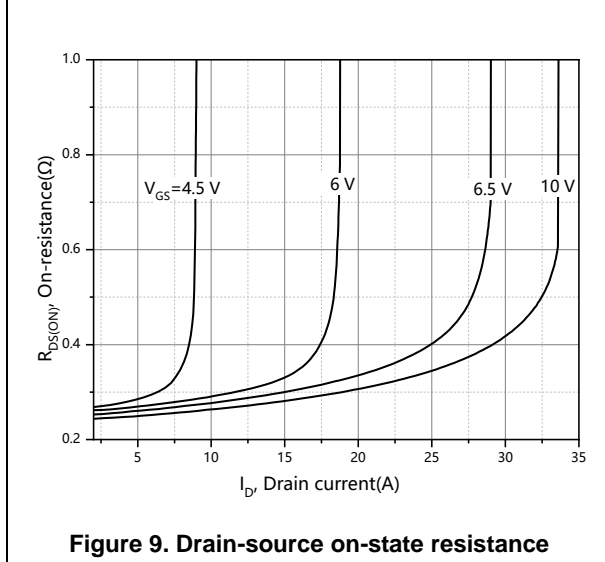
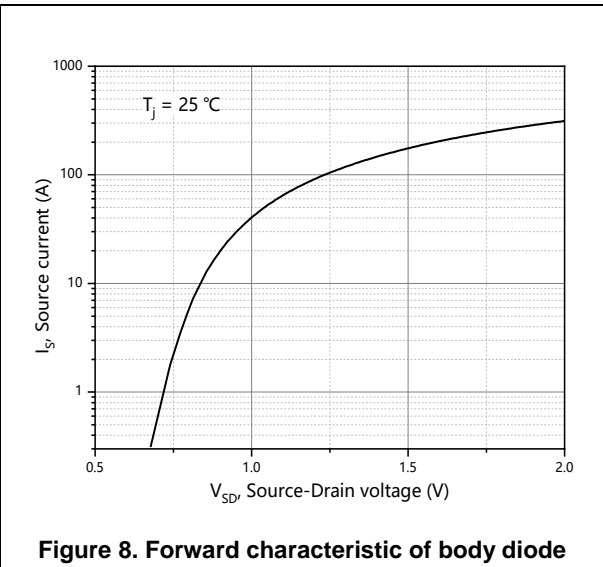
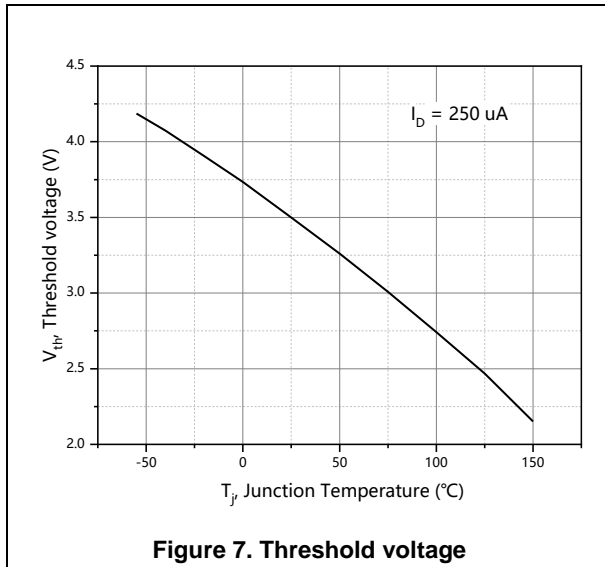
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=15\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		313.7		ns	$V_R=400\text{ V}$, $I_S=7.5\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		4.2		μC	
Peak reverse recovery current	I_{rrm}		25.2		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams





Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

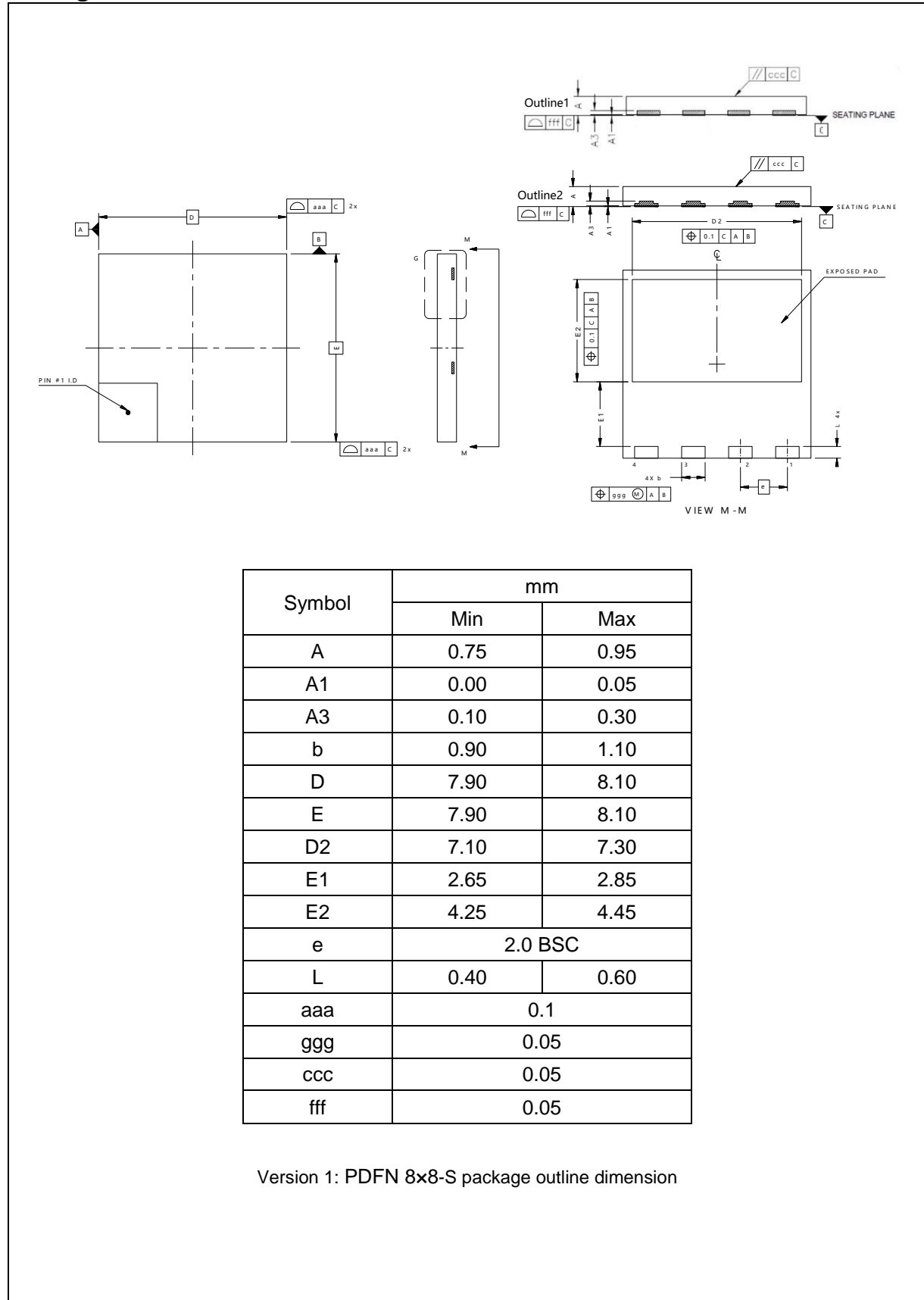


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Version 1: PDFN 8x8-S package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
PDFN 8x8-S	3000	1	3000	10	30000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG80R300JF	PDFN 8x8	yes	yes	yes

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